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Atty. Dkt AMAT/5621.Y1/DISPLAY/AKT/RKK**IN THE CLAIMS:**

Please amend the claims as follows:

1-70. (Canceled)

71. (Previously Presented) A method of fabricating multiple optical devices on a substrate, comprising:

positioning a substrate in a first processing chamber;
depositing a lower cladding on the substrate;
densifying the deposited lower cladding;
positioning the substrate in a second processing chamber;
depositing a core layer on the lower cladding;
patterning and etching the core layer to define a pattern of optical devices;
positioning the substrate in a third processing chamber; and
depositing an upper cladding over the patterned optical devices.

72. (Original) The method of claim 71 wherein the upper cladding is densified following deposition thereof.

73. (Previously Presented) The method of claim 71 wherein the substrate defines one or more die and the die have one or more optical devices formed thereon and further have a major dimension greater than a minor dimension.

74. (Previously Presented) The method of claim 71 wherein the utilization of the substrate is greater than about 75%.

75. (Currently Amended) The method of claim ~~72~~ 73 wherein the devices formed on a single die cover an area of at least about 400 cm².

76. (Previously Presented) The method of claim 73 wherein a single die comprising one or more optical devices has a shape similar to the substrate.

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77. (Original) The method of claim 73 wherein the deposition steps are performed in one or more processing systems wherein each deposition step requiring densification is performed on a system having at least one deposition chamber and at least one densification chamber.
78. (Original) The method of claim 73 wherein the die and the substrate have the same form factor.
79. (Currently Amended) The method of claim 73 wherein ~~the~~ at least two sides of a die of the one or more die are parallel to at least two sides of the substrate on which the die are formed.
80. (Currently Amended) The method of claim 71 wherein the substrate is ~~400mm~~ 400 mm by ~~500mm~~ 500 mm.
81. (Currently Amended) The method of claim 71 wherein the substrate has an area of about ~~400cm²~~ 400 cm² or greater.
82. (Previously Presented) The method of claim 71 wherein the substrate is a TFT panel.
83. (Previously Presented) The method of claim 71 wherein the substrate is made of a material selected from the group consisting of quartz, silica, fused silica or combinations thereof.
84. (Currently Amended) The method of claim 71 wherein the lower cladding is made of a material selected from the group consisting of USG, undoped silica, ~~or~~ and combinations thereof.
85. (Previously Presented) The method of claim 84 wherein the core layer is

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made of a material selected from the group consisting of PSG, GeO₂, SiON, Si₃N₄, and silicon.

86. (Previously Presented) The method of claim 85 wherein the upper cladding is made of a material selected from the group consisting of BPSG.

87. (Previously Presented) The method of claim 71 wherein the depositing a lower cladding and the densifying the lower cladding are performed on the same processing system.

88-97. (Canceled)

98. (Previously Presented) A method for forming a portion of an optical device on a substrate, comprising:

positioning a substrate in a first deposition chamber on a processing system;

depositing a lower cladding layer on the substrate;

positioning the substrate in a densification chamber on the same processing system and treating the substrate therein;

positioning the substrate in a second deposition chamber to deposit a core layer on the lower cladding layer; and then

positioning the substrate in the densification chamber on the processing system and treating the substrate therein.

99. (Original) The method of claim 98 wherein the lower cladding layer comprises USG and the core layer comprises PSG.

100. (Original) The method of claim 99 wherein treating the substrate in the densification chamber comprises exposing the substrate to a rapid thermal anneal process.

101. (Original) The method of claim 100 wherein the substrate is heated to a

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temperature above about 1000°C.

102. (Original) The method of claim 100 further comprising performing lithography steps on the substrate to define a core pattern and then depositing an upper cladding on the core pattern and then treating the substrate in a densification chamber.

103. (Currently Amended) The method of claim 102 wherein the substrate has an area of at least about ~~400cm²~~ 400 cm².

104. (Previously Presented) The method of claim 103 wherein the substrate has a major side longer than a minor side.

105. (Previously Presented) The method of claim 103 wherein the substrate is made of a material selected from the group consisting of quartz, silica, and fused silica.

106-113. (Canceled)